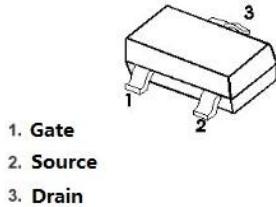


SOT-23N沟道60V漏-源电压MOS管  
N-Channel 60V(D-S) Mosfet

产品特性总结Product Summary	
VDS	60V
RDS(on)(@VGS= 10V)	<70mΩ
RDS(on)(@VGS= 4.5V)	<90mΩ

根据客户要求打印 According  
to customer requirement

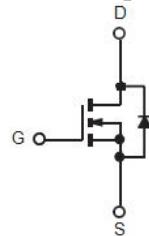
## 脚位定义 Pin Definition

特征 Features

- 低导通电阻Low Rds(on)@VGS= 10V
- 沟道功率MOS管TrenchFET Power MOSFET
- 无卤、RoHS认证Halogen-free、RoHS Compliant
- 表贴型封装Surface Mount Package

应用 Applications

- 便携式设备的直流/直流转换DC/DC Converter for Portable Devices
- 负载开关Load Switch
- 电池开关Battery switch

等效电路 Equivalent circuit

极限值和温度特性(TA = 25°C 除非另有规定)

**Maximum Ratings & Thermal Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified.)

参数 Parameters	符号 Symbol	数值 Value	单位 Unit
漏源电压Drain-Source Voltage	V <sub>DS</sub>	60	V
栅源电压Gate-Source Voltage	V <sub>GS</sub>	±16	V
漏极连续电流Continuous Drain Current	I <sub>D</sub>	3.8	A
漏极脉冲电流Pulsed Drain Current (note 1)	I <sub>DM</sub>	15.2	A
最大功耗Maximum Power Dissipation	P <sub>D</sub>	1.56	W
结环热阻Thermal Resistance from Junction to Ambient (note 2)	R <sub>θJA</sub>	80	°C/W
结温和存储温度Junction and Storage Temperature	T <sub>J</sub> 、T <sub>STG</sub>	-50~+150	°C

电特性 (TA = 25°C 除非另有规定)

**Electrical Characteristics** (Ratings at 25°C ambient temperature unless otherwise specified).

参数 Parameters	符号 Symbol	测试条件 Test Condition	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
<b>静态特性Static Characteristics</b>						
漏源击穿电压 Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60	--	--	V
零栅压漏极电流 Zero gate voltage drain current	I <sub>dss</sub>	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	--	--	1	μA
栅源漏电流Gate-body leakage current	I <sub>gss</sub>	V <sub>GS</sub> = ± 16V, V <sub>DS</sub> = 0V	--	--	±100	nA
栅源阈值电压 Gate threshold voltage (note 3)	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.0	2.0	3.0	V
漏源极导通电阻 Drain-source on-resistance (note 3)	R <sub>D(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3A	--	57	70	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2A	--	66	90	mΩ
二极管正向电压 Diode forward voltage (note 3)	V <sub>SD</sub>	I <sub>S</sub> = 2A, V <sub>GS</sub> = 0V	--	0.79	1.2	V

动态特性Dynamic Characteristics (note4)						
输入电容Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15V, V <sub>GS</sub> =0V, f=1MHz	--	362	--	pF
输出电容Output Capacitance	C <sub>oss</sub>		--	23	--	pF
反向传输电容 Reverse Transfer Capacitance	C <sub>rss</sub>		--	16	--	pF
开关特性Switching Characteristics (note 4)						
开启延迟时间Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 30V, I <sub>D</sub> = 1A, R <sub>G</sub> = 3.3Ω, V <sub>GS</sub> = 10V	--	3.4	--	ns
开启上升沿时间Turn-on rise time	t <sub>r</sub>		--	5.8	--	ns
关断延迟时间Turn-off delay time	t <sub>d(off)</sub>		--	21	--	ns
关断下降沿时间Turn-off fall time	t <sub>f</sub>		--	4.6	--	ns
总栅极电荷Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 30V, I <sub>D</sub> =4A, V <sub>GS</sub> =10V	--	6.9	--	nC
栅源电荷Gate-Source Charge	Q <sub>gs</sub>		--	0.9	--	nC
栅漏电荷Gate-Drain Charge	Q <sub>gd</sub>		--	1.8	--	nC

**\*Notes :**

1. Repetitive rating: Pulse width limited by maximum junction temperature
2. Surface Mounted on FR4 board, t≤10 sec.
3. Pulse test : Pulse width≤300μs, duty cycle≤2%.
4. Guaranteed by design, not subject to production.

## 典型特性曲线 Typical characteristics

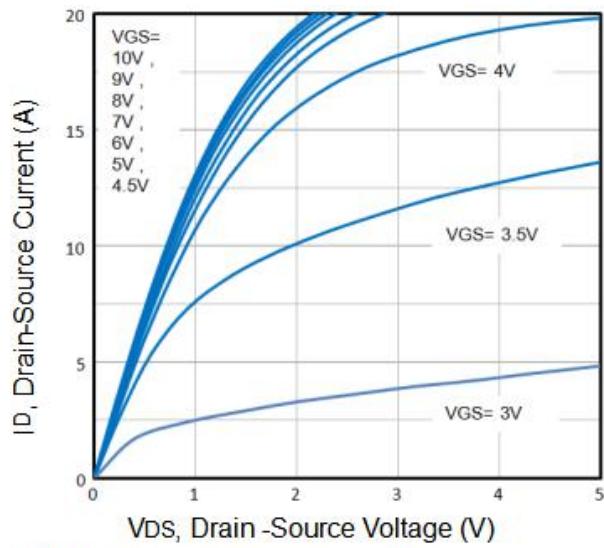


Fig1. Typical Output Characteristics

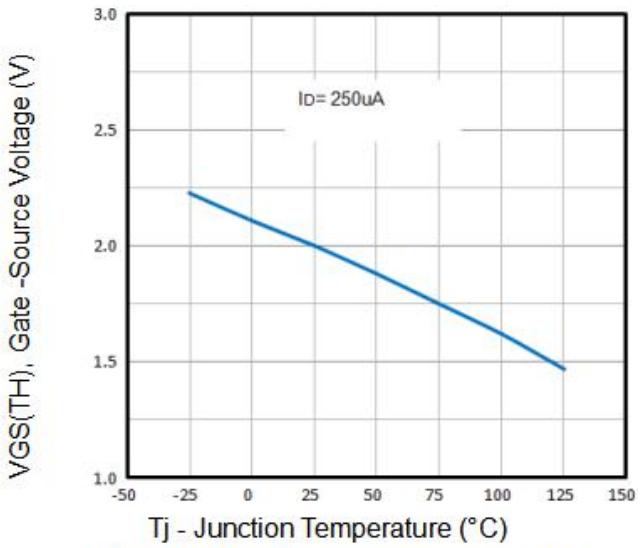


Fig2.  $V_{GS(TH)}$  Voltage Vs. Temperature

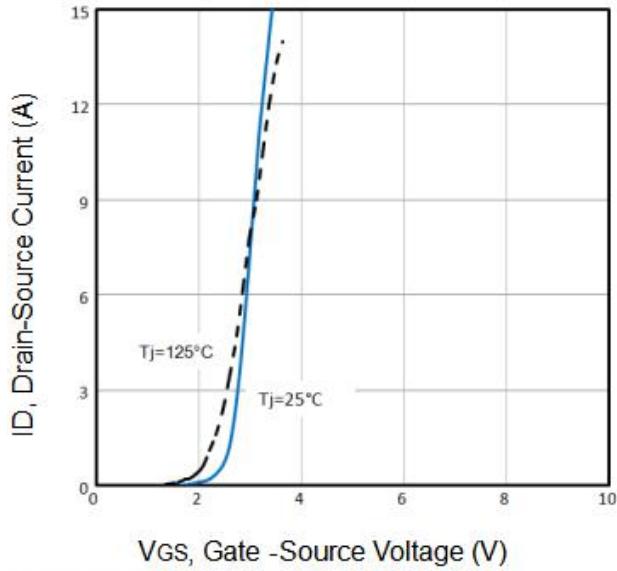


Fig3. Typical Transfer Characteristics

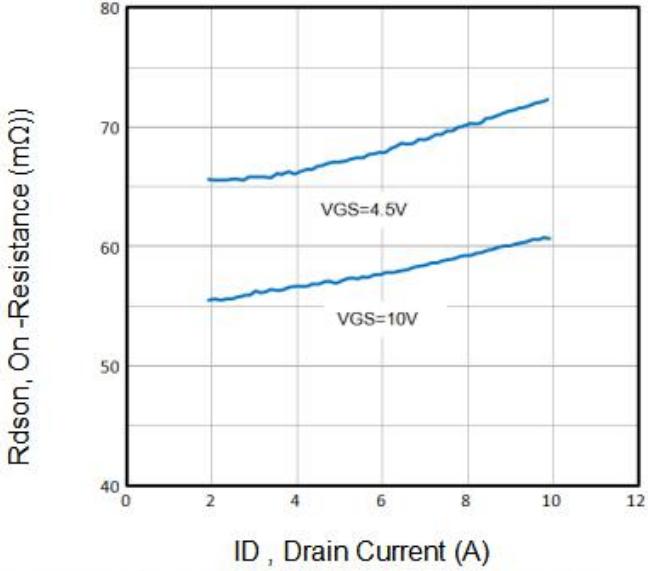


Fig4. On-Resistance vs. Drain Current and Gate

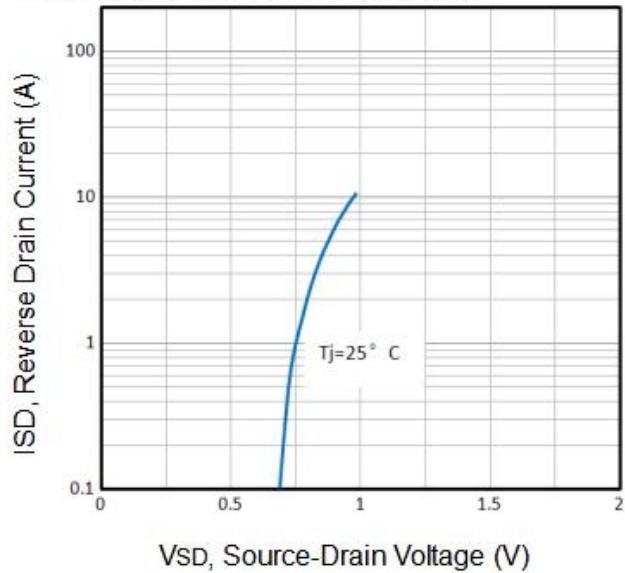


Fig5. Typical Source-Drain Diode Forward Voltage

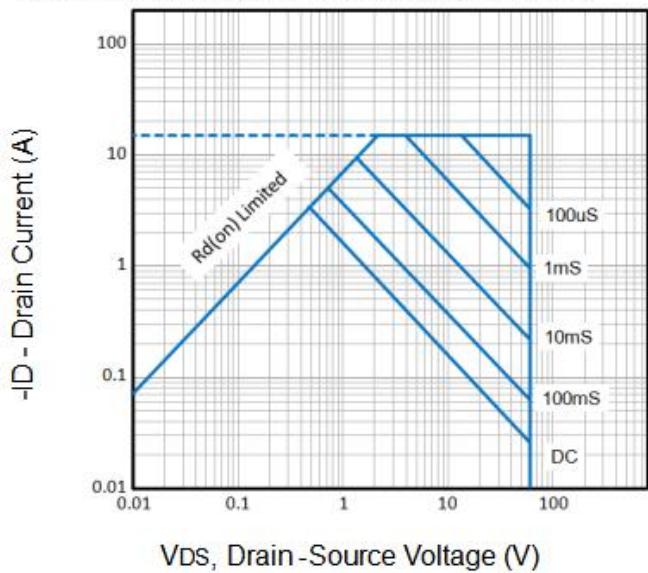
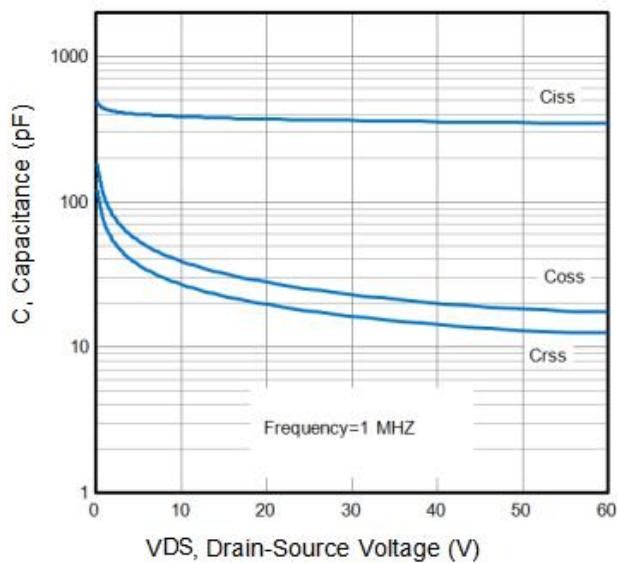
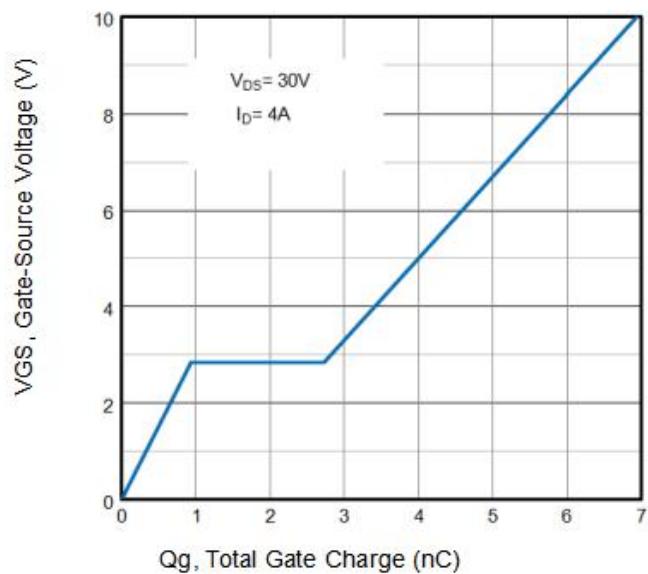
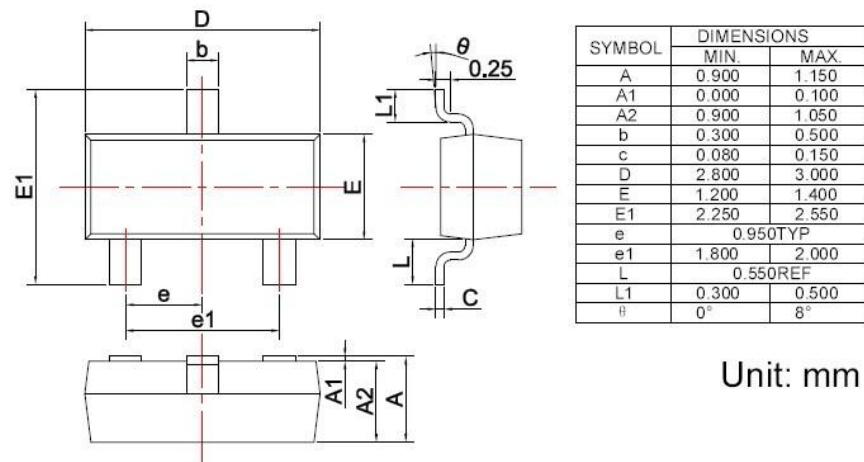


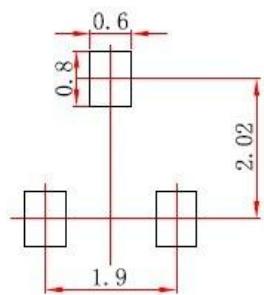
Fig6. Maximum Safe Operating Area

**Fig7.** Typical Capacitance Vs. Drain-Source Voltage**Fig8.** Typical Gate Charge Vs. Gate-Source Voltage

### 封装外形图 SOT-23 Package Outline Dimensions



### 焊盘设计参考PCB Design



Note:  
1. Controlling dimension: In millimeters.  
2. General tolerance:  $\pm 0.05$ mm.  
3. The pad layout is for reference purposes only.